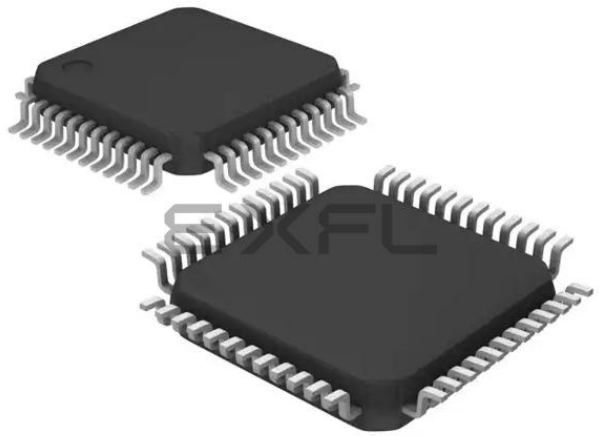

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Details	
Product Status	Active
Core Processor	12V1
Core Size	16-Bit
Speed	25MHz
Connectivity	CANbus, IrDA, LINbus, SCI, SPI
Peripherals	LVD, POR, PWM, WDT
Number of I/O	40
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	3.13V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/s9s12g128f0mlf

Chapter 14
Analog-to-Digital Converter (ADC12B12CV2)

Chapter 15
Analog-to-Digital Converter (ADC10B16CV2)

Table 2-76. PT1AD Register Field Descriptions

Field	Description
7-0 PT1AD	**Port AD general-purpose input/output data**—Data Register When not used with an alternative signal, the associated pin can be used as general-purpose I/O. In general-purpose output mode the port data register bit value is driven to the pin. If the associated data direction bit is set to 1, a read returns the value of the port data register bit, otherwise the buffered pin input state is read if the digital input buffers are enabled (Section 2.3.12, “Pins AD15-0”).

2.4.3.51 Port AD Input Register (PTI0AD)

Address 0x0272 (G1, G2) Access: User read only[1]

	7	6	5	4	3	2	1	0
R	PTI0AD7	PTI0AD6	PTI0AD5	PTI0AD4	PTI0AD3	PTI0AD2	PTI0AD1	PTI0AD0
W								
Reset	0	0	0	0	0	0	0	0

Address 0x0272 (G3) Access: User read only[1]

	7	6	5	4	3	2	1	0
R	0	0	0	0	PTI0AD3	PTI0AD2	PTI0AD1	PTI0AD0
W								
Reset	0	0	0	0	0	0	0	0

Figure 2-51. Port AD Input Register (PTI0AD)

[1] Read: Anytime
Write: Never

Table 2-77. PTI0AD Register Field Descriptions

Field	Description
7-0 PTI0AD	**Port AD input data**— A read always returns the buffered input state of the associated pin. It can be used to detect overload or short circuit conditions on output pins.

2.4.3.52 Port AD Input Register (PTI1AD)

Address 0x0273 Access: User read only[1]

	7	6	5	4	3	2	1	0
R	PTI1AD7	PTI1AD6	PTI1AD5	PTI1AD4	PTI1AD3	PTI1AD2	PTI1AD1	PTI1AD0
W								
Reset	0	0	0	0	0	0	0	0

Figure 2-52. Port AD Input Register (PTI1AD)

[1] Read: Anytime
Write: Never

Chapter 6
Interrupt Module (S12SINTV1)

Version Number	Revision Date	Effective Date	Author	Description of Changes
01.02	13 Sep 2007			updates for S12P family devices: - re-added XIRQ and IRQ references since this functionality is used on devices without D2D - added low voltage reset as possible source to the pin reset vector
01.03	21 Nov 2007			added clarification of “Wake-up from STOP or WAIT by XIRQ with X bit set” feature
01.04	20 May 2009			added footnote about availability of “Wake-up from STOP or WAIT by XIRQ with X bit set” feature

6.1 Introduction

The INT module decodes the priority of all system exception requests and provides the applicable vector for processing the exception to the CPU. The INT module supports:

- I bit and X bit maskable interrupt requests
- A non-maskable unimplemented op-code trap
- A non-maskable software interrupt (SWI) or background debug mode request
- Three system reset vector requests
- A spurious interrupt vector

Each of the I bit maskable interrupt requests is assigned to a fixed priority level.

6.1.1 Glossary

Table 6-2 contains terms and abbreviations used in the document.

Table 6-2. Terminology

Term	Meaning
CCR	Condition Code Register (in the CPU)
ISR	Interrupt Service Routine
MCU	Micro-Controller Unit

6.1.2 Features

- Interrupt vector base register (IVBR)
- One spurious interrupt vector (at address vector base[1] + 0x0080).

Since the host knows the target serial clock frequency, the SYNC command (used to abort a command) does not need to consider the lower possible target frequency. In this case, the host could issue a SYNC very close to the 128 serial clock cycles length. Providing a small overhead on the pulse length in order to assure the SYNC pulse will not be misinterpreted by the target. See Section 7.4.9, “SYNC — Request Timed Reference Pulse”.

Figure 7-12 shows a SYNC command being issued after a READ_BYTE, which aborts the READ_BYTE command. Note that, after the command is aborted a new command could be issued by the host computer.

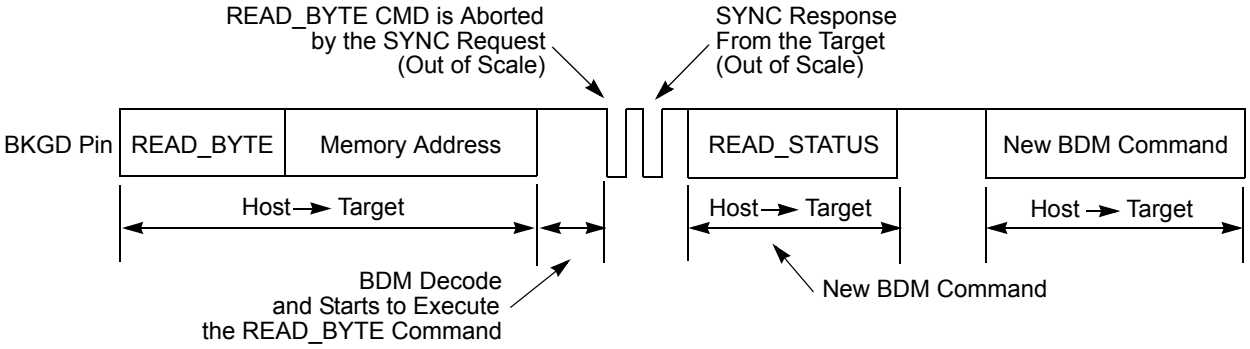

Figure 7-12. ACK Abort Procedure at the Command Level

NOTE

Figure 7-12 does not represent the signals in a true timing scale

Figure 7-13 shows a conflict between the ACK pulse and the SYNC request pulse. This conflict could occur if a POD device is connected to the target BKGD pin and the target is already in debug active mode. Consider that the target CPU is executing a pending BDM command at the exact moment the POD is being connected to the BKGD pin. In this case, an ACK pulse is issued along with the SYNC command. In this case, there is an electrical conflict between the ACK speedup pulse and the SYNC pulse. Since this is not a probable situation, the protocol does not prevent this conflict from happening.

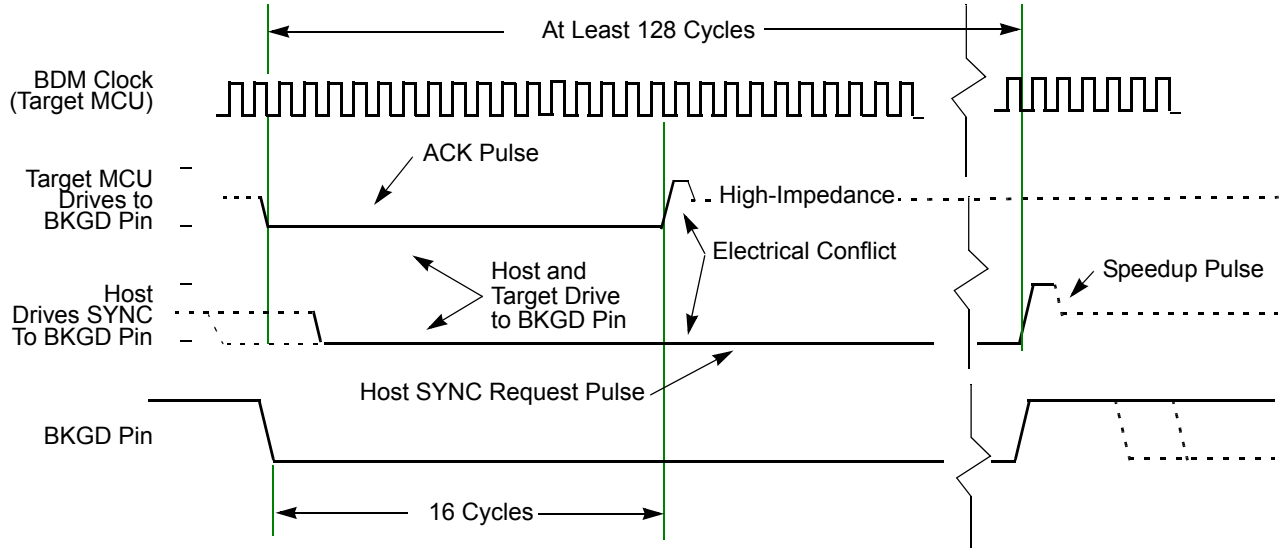

Figure 7-13. ACK Pulse and SYNC Request Conflict

Table 8-16. State1 Sequencer Next State Selection

SC[3:0]	Description (Unspecified matches have no effect)
1010	Reserved
1011	Reserved
1100	Reserved
1101	Either Match0 or Match2 to Final State.....Match1 to State2
1110	Reserved
1111	Reserved

The priorities described in Table 8-36 dictate that in the case of simultaneous matches, a match leading to final state has priority followed by the match on the lower channel number (0,1,2). Thus with SC[3:0]=1101 a simultaneous match0/match1 transitions to final state.

8.3.2.7.2 Debug State Control Register 2 (DBGSCR2)

Address: 0x0027

	7	6	5	4	3	2	1	0
R	0	0	0	0	SC3	SC2	SC1	SC0
W								
Reset	0	0	0	0	0	0	0	0

= Unimplemented or Reserved

Figure 8-10. Debug State Control Register 2 (DBGSCR2)

Read: If COMRV[1:0] = 01

Write: If COMRV[1:0] = 01 and DBG is not armed.

This register is visible at 0x0027 only with COMRV[1:0] = 01. The state control register 2 selects the targeted next state whilst in State2. The matches refer to the match channels of the comparator match control logic as depicted in Figure 8-1 and described in Section 8.3.2.8.1, “Debug Comparator Control Register (DBGXCTL). Comparators must be enabled by setting the comparator enable bit in the associated DBGXCTL control register.

Table 8-17. DBGSCR2 Field Descriptions

Field	Description
3–0 SC[3:0]	These bits select the targeted next state whilst in State2, based upon the match event.

Table 8-18. State2 —Sequencer Next State Selection

SC[3:0]	Description (Unspecified matches have no effect)
0000	Match0 to State1..... Match2 to State3.
0001	Match1 to State3
0010	Match2 to State3
0011	Match1 to State3..... Match0 Final State
0100	Match1 to State1..... Match2 to State3.

8.4.5.1.1 Storing with Begin Trigger Alignment

Storing with begin alignment, data is not stored in the Trace Buffer until the Final State is entered. Once the trigger condition is met the DBG module remains armed until 64 lines are stored in the Trace Buffer. If the trigger is at the address of the change-of-flow instruction the change of flow associated with the trigger is stored in the Trace Buffer. Using begin alignment together with tagging, if the tagged instruction is about to be executed then the trace is started. Upon completion of the tracing session the breakpoint is generated, thus the breakpoint does not occur at the tagged instruction boundary.

8.4.5.1.2 Storing with End Trigger Alignment

Storing with end alignment, data is stored in the Trace Buffer until the Final State is entered, at which point the DBG module becomes disarmed and no more data is stored. If the trigger is at the address of a change of flow instruction, the trigger event is not stored in the Trace Buffer. If all trace buffer lines have been used before a trigger event occurrs then the trace continues at the first line, overwriting the oldest entries.

8.4.5.2 Trace Modes

Four trace modes are available. The mode is selected using the TRCMOD bits in the DBGTCR register. Tracing is enabled using the TSOURCE bit in the DBGTCR register. The modes are described in the following subsections.

8.4.5.2.1 Normal Mode

In Normal Mode, change of flow (COF) program counter (PC) addresses are stored.

COF addresses are defined as follows:

- Source address of taken conditional branches (long, short, bit-conditional, and loop primitives)
- Destination address of indexed JMP, JSR, and CALL instruction
- Destination address of RTI, RTS, and RTC instructions
- Vector address of interrupts, except for BDM vectors

LBRA, BRA, BSR, BGND as well as non-indexed JMP, JSR, and CALL instructions are not classified as change of flow and are not stored in the trace buffer.

Stored information includes the full 18-bit address bus and information bits, which contains a source/destination bit to indicate whether the stored address was a source address or destination address.

NOTE

When a COF instruction with destination address is executed, the destination address is stored to the trace buffer on instruction completion, indicating the COF has taken place. If an interrupt occurs simultaneously then the next instruction carried out is actually from the interrupt service routine. The instruction at the destination address of the original program flow gets executed after the interrupt service routine.

Address	Name		Bit 7	6	5	4	3	2	1	Bit 0
0x0003	ATDCTL3	R	DJM	S8C	S4C	S2C	S1C	FIFO	FRZ1	FRZ0
		W								
0x0004	ATDCTL4	R	SMP2	SMP1	SMP0	PRS[4:0]				
		W								
0x0005	ATDCTL5	R	0	SC	SCAN	MULT	CD	CC	CB	CA
		W								
0x0006	ATDSTAT0	R	SCF	0	ETORF	FIFOR	CC3	CC2	CC1	CC0
		W								
0x0007	Unimple-mented	R	0	0	0	0	0	0	0	0
		W								
0x0008	ATDCMPEH	R	0	0	0	0	0	0	0	0
		W								
0x0009	ATDCMPEL	R	CMPE[7:0]							
		W								
0x000A	ATDSTAT2H	R	0	0	0	0	0	0	0	0
		W								
0x000B	ATDSTAT2L	R	CCF[7:0]							
		W								
0x000C	ATDDIENH	R	1	1	1	1	1	1	1	1
		W								
0x000D	ATDDIENL	R	IEN[7:0]							
		W								
0x000E	ATDCMPHTH	R	0	0	0	0	0	0	0	0
		W								
0x000F	ATDCMPHTL	R	CMPHT[7:0]							
		W								
0x0010	ATDDR0	R	See Section 11.3.2.12.1, “Left Justified Result Data (DJM=0)” and Section 11.3.2.12.2, “Right Justified Result Data (DJM=1)”							
		W								
0x0012	ATDDR1	R	See Section 11.3.2.12.1, “Left Justified Result Data (DJM=0)” and Section 11.3.2.12.2, “Right Justified Result Data (DJM=1)”							
		W								
0x0014	ATDDR2	R	See Section 11.3.2.12.1, “Left Justified Result Data (DJM=0)” and Section 11.3.2.12.2, “Right Justified Result Data (DJM=1)”							
		W								
0x0016	ATDDR3	R	See Section 11.3.2.12.1, “Left Justified Result Data (DJM=0)” and Section 11.3.2.12.2, “Right Justified Result Data (DJM=1)”							
		W								
0x0018	ATDDR4	R	See Section 11.3.2.12.1, “Left Justified Result Data (DJM=0)” and Section 11.3.2.12.2, “Right Justified Result Data (DJM=1)”							
		W								
0x001A	ATDDR5	R	See Section 11.3.2.12.1, “Left Justified Result Data (DJM=0)” and Section 11.3.2.12.2, “Right Justified Result Data (DJM=1)”							
		W								
0x001C	ATDDR6	R	See Section 11.3.2.12.1, “Left Justified Result Data (DJM=0)” and Section 11.3.2.12.2, “Right Justified Result Data (DJM=1)”							
		W								
0x001E	ATDDR7	R	See Section 11.3.2.12.1, “Left Justified Result Data (DJM=0)” and Section 11.3.2.12.2, “Right Justified Result Data (DJM=1)”							
		W								
0x0020 - 0x002F	Unimple-mented	R	0	0	0	0	0	0	0	0
		W								

= Unimplemented or Reserved

Figure 11-2. ADC10B8C Register Summary (Sheet 2 of 2)

12.1.1 Features

- 8-, 10-, or 12-bit resolution.
- Automatic return to low power after conversion sequence
- Automatic compare with interrupt for higher than or less/equal than programmable value
- Programmable sample time.
- Left/right justified result data.
- External trigger control.
- Sequence complete interrupt.
- Analog input multiplexer for 8 analog input channels.
- Special conversions for VRH, VRL, (VRL+VRH)/2.
- 1-to-8 conversion sequence lengths.
- Continuous conversion mode.
- Multiple channel scans.
- Configurable external trigger functionality on any AD channel or any of four additional trigger inputs. The four additional trigger inputs can be chip external or internal. Refer to device specification for availability and connectivity.
- Configurable location for channel wrap around (when converting multiple channels in a sequence).

20.1.2 Features

The SCI includes these distinctive features:

- Full-duplex or single-wire operation
- Standard mark/space non-return-to-zero (NRZ) format
- Selectable IrDA 1.4 return-to-zero-inverted (RZI) format with programmable pulse widths
- 13-bit baud rate selection
- Programmable 8-bit or 9-bit data format
- Separately enabled transmitter and receiver
- Programmable polarity for transmitter and receiver
- Programmable transmitter output parity
- Two receiver wakeup methods:
  - Idle line wakeup
  - Address mark wakeup
- Interrupt-driven operation with eight flags:
  - Transmitter empty
  - Transmission complete
  - Receiver full
  - Idle receiver input
  - Receiver overrun
  - Noise error
  - Framing error
  - Parity error
  - Receive wakeup on active edge
  - Transmit collision detect supporting LIN
  - Break Detect supporting LIN
- Receiver framing error detection
- Hardware parity checking
- 1/16 bit-time noise detection

20.1.3 Modes of Operation

The SCI functions the same in normal, special, and emulation modes. It has two low power modes, wait and stop modes.

- Run mode
- Wait mode
- Stop mode

Table 24-34. Erase Verify P-Flash Section Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x03	Global address [17:16] of a P-Flash block
001	Global address [15:0] of the first phrase to be verified	
010	Number of phrases to be verified	

Upon clearing CCIF to launch the Erase Verify P-Flash Section command, the Memory Controller will verify the selected section of Flash memory is erased. The CCIF flag will set after the Erase Verify P-Flash Section operation has completed. If the section is not erased, it means blank check failed, both MGSTAT bits will be set.

Table 24-35. Erase Verify P-Flash Section Command Error Handling

Register	Error Bit	Error Condition
FSTAT	ACCERR	Set if CCOBIX[2:0] != 010 at command launch
		Set if command not available in current mode (see Table 24-25)
		Set if an invalid global address [17:0] is supplied see Table 24-3)[1]
		Set if a misaligned phrase address is supplied (global address [2:0] != 000)
		Set if the requested section crosses a the P-Flash address boundary
	FPVIOL	None
	MGSTAT1	Set if any errors have been encountered during the read[2] or if blank check failed.
	MGSTAT0	Set if any non-correctable errors have been encountered during the read[2] or if blank check failed.

1 As defined by the memory map for FTMRG32K1.

2 As found in the memory map for FTMRG32K1.

24.4.6.4 Read Once Command

The Read Once command provides read access to a reserved 64 byte field (8 phrases) located in the nonvolatile information register of P-Flash. The Read Once field is programmed using the Program Once command described in Section 24.4.6.6. The Read Once command must not be executed from the Flash block containing the Program Once reserved field to avoid code runaway.

Table 24-36. Read Once Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x04	Not Required
001	Read Once phrase index (0x0000 - 0x0007)	
010	Read Once word 0 value	
011	Read Once word 1 value	
100	Read Once word 2 value	

Table 25-61. Erase Verify EEPROM Section Command Error Handling

Register	Error Bit	Error Condition
FSTAT	ACCERR	Set if CCOBIX[2:0] != 010 at command launch
		Set if command not available in current mode (see Table 25-27)
		Set if an invalid global address [17:0] is supplied
		Set if a misaligned word address is supplied (global address [0] != 0)
		Set if the requested section breaches the end of the EEPROM block
	FPVIOL	None
	MGSTAT1	Set if any errors have been encountered during the read or if blank check failed.
	MGSTAT0	Set if any non-correctable errors have been encountered during the read or if blank check failed.

25.4.6.15 Program EEPROM Command

The Program EEPROM operation programs one to four previously erased words in the EEPROM block. The Program EEPROM operation will confirm that the targeted location(s) were successfully programmed upon completion.

CAUTION

A Flash word must be in the erased state before being programmed. Cumulative programming of bits within a Flash word is not allowed.

Table 25-62. Program EEPROM Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x11	Global address [17:16] to identify the EEPROM block
001	Global address [15:0] of word to be programmed	
010	Word 0 program value	
011	Word 1 program value, if desired	
100	Word 2 program value, if desired	
101	Word 3 program value, if desired	

Upon clearing CCIF to launch the Program EEPROM command, the user-supplied words will be transferred to the Memory Controller and be programmed if the area is unprotected. The CCOBIX index value at Program EEPROM command launch determines how many words will be programmed in the EEPROM block. The CCIF flag is set when the operation has completed.

During the reset sequence, fields DPOPEN and DPS of the EEPROT register are loaded with the contents of the EEPROM protection byte in the Flash configuration field at global address 0x3_FF0D located in P-Flash memory (see Table 26-4) as indicated by reset condition F in Table 26-23. To change the EEPROM protection that will be loaded during the reset sequence, the P-Flash sector containing the EEPROM protection byte must be unprotected, then the EEPROM protection byte must be programmed. If a double bit fault is detected while reading the P-Flash phrase containing the EEPROM protection byte during the reset sequence, the DPOPEN bit will be cleared and DPS bits will be set to leave the EEPROM memory fully protected.

Trying to alter data in any protected area in the EEPROM memory will result in a protection violation error and the FPVIOL bit will be set in the FSTAT register. Block erase of the EEPROM memory is not possible if any of the EEPROM sectors are protected.

Table 26-22. EEPROT Field Descriptions

Field	Description
7 DPOPEN	EEPROM Protection Control 0 Enables EEPROM memory protection from program and erase with protected address range defined by DPS bits 1 Disables EEPROM memory protection from program and erase
5–0 DPS[5:0]	**EEPROM Protection Size** — The DPS[5:0] bits determine the size of the protected area in the EEPROM memory as shown in Table 26-23 .

Table 26-23. EEPROM Protection Address Range

DPS[5:0]	Global Address Range	Protected Size
000000	0x0_0400 – 0x0_041F	32 bytes
000001	0x0_0400 – 0x0_043F	64 bytes
000010	0x0_0400 – 0x0_045F	96 bytes
000011	0x0_0400 – 0x0_047F	128 bytes
000100	0x0_0400 – 0x0_049F	160 bytes
000101	0x0_0400 – 0x0_04BF	192 bytes
The Protection Size goes on enlarging in step of 32 bytes, for each DPS value increasing of one. . . .		
101111 - to - 111111	0x0_0400 – 0x0_09FF	1,536 bytes

Table 27-36. Erase Verify P-Flash Section Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x03	Global address [17:16] of a P-Flash block
001	Global address [15:0] of the first phrase to be verified	
010	Number of phrases to be verified	

Upon clearing CCIF to launch the Erase Verify P-Flash Section command, the Memory Controller will verify the selected section of Flash memory is erased. The CCIF flag will set after the Erase Verify P-Flash Section operation has completed. If the section is not erased, it means blank check failed, both MGSTAT bits will be set.

Table 27-37. Erase Verify P-Flash Section Command Error Handling

Register	Error Bit	Error Condition
FSTAT	ACCERR	Set if CCOBIX[2:0] != 010 at command launch
		Set if command not available in current mode (see Table 27-27)
		Set if an invalid global address [17:0] is supplied see Table 27-3)
		Set if a misaligned phrase address is supplied (global address [2:0] != 000)
		Set if the requested section crosses a the P-Flash address boundary
	FPVIOL	None
	MGSTAT1	Set if any errors have been encountered during the read or if blank check failed.
	MGSTAT0	Set if any non-correctable errors have been encountered during the read or if blank check failed.

27.4.6.4 Read Once Command

The Read Once command provides read access to a reserved 64 byte field (8 phrases) located in the nonvolatile information register of P-Flash. The Read Once field is programmed using the Program Once command described in Section 27.4.6.6. The Read Once command must not be executed from the Flash block containing the Program Once reserved field to avoid code runaway.

Table 27-38. Read Once Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x04	Not Required
001	Read Once phrase index (0x0000 - 0x0007)	
010	Read Once word 0 value	
011	Read Once word 1 value	
100	Read Once word 2 value	
101	Read Once word 3 value	

Table 28-28. P-Flash Commands

FCMD	Command	Function on P-Flash Memory
0x02	Erase Verify Block	Verify that a P-Flash block is erased.
0x03	Erase Verify P-Flash Section	Verify that a given number of words starting at the address provided are erased.
0x04	Read Once	Read a dedicated 64 byte field in the nonvolatile information register in P-Flash block that was previously programmed using the Program Once command.
0x06	Program P-Flash	Program a phrase in a P-Flash block.
0x07	Program Once	Program a dedicated 64 byte field in the nonvolatile information register in P-Flash block that is allowed to be programmed only once.
0x08	Erase All Blocks	Erase all P-Flash (and EEPROM) blocks. An erase of all Flash blocks is only possible when the FPLDIS, FPHDIS, and FPOPEN bits in the FPROT register and the DPOPEN bit in the EEPROT register are set prior to launching the command.
0x09	Erase Flash Block	Erase a P-Flash (or EEPROM) block. An erase of the full P-Flash block is only possible when FPLDIS, FPHDIS and FPOPEN bits in the FPROT register are set prior to launching the command.
0x0A	Erase P-Flash Sector	Erase all bytes in a P-Flash sector.
0x0B	Unsecure Flash	Supports a method of releasing MCU security by erasing all P-Flash (and EEPROM) blocks and verifying that all P-Flash (and EEPROM) blocks are erased.
0x0C	Verify Backdoor Access Key	Supports a method of releasing MCU security by verifying a set of security keys.
0x0D	Set User Margin Level	Specifies a user margin read level for all P-Flash blocks.
0x0E	Set Field Margin Level	Specifies a field margin read level for all P-Flash blocks (special modes only).

28.4.4.5 EEPROM Commands

Table 28-29 summarizes the valid EEPROM commands along with the effects of the commands on the EEPROM block.

Table 28-29. EEPROM Commands

FCMD	Command	Function on EEPROM Memory
0x01	Erase Verify All Blocks	Verify that all EEPROM (and P-Flash) blocks are erased.
0x02	Erase Verify Block	Verify that the EEPROM block is erased.

28.4.6 Flash Command Description

This section provides details of all available Flash commands launched by a command write sequence. The ACCERR bit in the FSTAT register will be set during the command write sequence if any of the following illegal steps are performed, causing the command not to be processed by the Memory Controller:

- Starting any command write sequence that programs or erases Flash memory before initializing the FCLKDIV register
- Writing an invalid command as part of the command write sequence
- For additional possible errors, refer to the error handling table provided for each command

If a Flash block is read during execution of an algorithm (CCIF = 0) on that same block, the read operation will return invalid data if both flags SFDIF and DFDIF are set. If the SFDIF or DFDIF flags were not previously set when the invalid read operation occurred, both the SFDIF and DFDIF flags will be set.

If the ACCERR or FPVIOL bits are set in the FSTAT register, the user must clear these bits before starting any command write sequence (see Section 28.3.2.7).

CAUTION

A Flash word or phrase must be in the erased state before being programmed. Cumulative programming of bits within a Flash word or phrase is not allowed.

28.4.6.1 Erase Verify All Blocks Command

The Erase Verify All Blocks command will verify that all P-Flash and EEPROM blocks have been erased.

Table 28-31. Erase Verify All Blocks Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x01	Not required

Upon clearing CCIF to launch the Erase Verify All Blocks command, the Memory Controller will verify that the entire Flash memory space is erased. The CCIF flag will set after the Erase Verify All Blocks operation has completed. If all blocks are not erased, it means blank check failed, both MGSTAT bits will be set.

Table 28-32. Erase Verify All Blocks Command Error Handling

Register	Error Bit	Error Condition
FSTAT	ACCERR	Set if CCOBIX[2:0] != 000 at command launch
	FPVIOL	None
	MGSTAT1	Set if any errors have been encountered during the read[1] or if blank check failed .
	MGSTAT0	Set if any non-correctable errors have been encountered during the read[1] or if blank check failed.

[1] As found in the memory map for FTMRG96K1.

29.4.6.13 Set Field Margin Level Command

The Set Field Margin Level command, valid in special modes only, causes the Memory Controller to set the margin level specified for future read operations of the P-Flash or EEPROM block.

Upon clearing CCIF to launch the Set Field Margin Level command, the Memory Controller will set the

Table 29-57. Set Field Margin Level Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x0E	Flash block selection code [1:0]. See Table 29-34
001	Margin level setting.	

field margin level for the targeted block and then set the CCIF flag.

NOTE

When the EEPROM block is targeted, the EEPROM field margin levels are applied only to the EEPROM reads. However, when the P-Flash block is targeted, the P-Flash field margin levels are applied to both P-Flash and EEPROM reads. It is not possible to apply field margin levels to the P-Flash block only.

Valid margin level settings for the Set Field Margin Level command are defined in Table 29-58.

Table 29-58. Valid Set Field Margin Level Settings

CCOB (CCOBIX=001)	Level Description
0x0000	Return to Normal Level
0x0001	User Margin-1 Level[1]
0x0002	User Margin-0 Level[2]
0x0003	Field Margin-1 Level[1]
0x0004	Field Margin-0 Level[2]

1 Read margin to the erased state

2 Read margin to the programmed state

31.4.6.15 Program EEPROM Command

The Program EEPROM operation programs one to four previously erased words in the EEPROM block. The Program EEPROM operation will confirm that the targeted location(s) were successfully programmed upon completion.

CAUTION

A Flash word must be in the erased state before being programmed. Cumulative programming of bits within a Flash word is not allowed.

Table 31-62. Program EEPROM Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x11	Global address [17:16] to identify the EEPROM block
001	Global address [15:0] of word to be programmed	
010	Word 0 program value	
011	Word 1 program value, if desired	
100	Word 2 program value, if desired	
101	Word 3 program value, if desired	

Upon clearing CCIF to launch the Program EEPROM command, the user-supplied words will be transferred to the Memory Controller and be programmed if the area is unprotected. The CCOBIX index value at Program EEPROM command launch determines how many words will be programmed in the EEPROM block. The CCIF flag is set when the operation has completed.

Table 31-63. Program EEPROM Command Error Handling

Register	Error Bit	Error Condition
FSTAT	ACCERR	Set if CCOBIX[2:0] < 010 at command launch
		Set if CCOBIX[2:0] > 101 at command launch
		Set if command not available in current mode (see Table 31-27)
		Set if an invalid global address [17:0] is supplied
		Set if a misaligned word address is supplied (global address [0] != 0)
		Set if the requested group of words breaches the end of the EEPROM block
	FPVIOL	Set if the selected area of the EEPROM memory is protected
	MGSTAT1	Set if any errors have been encountered during the verify operation
	MGSTAT0	Set if any non-correctable errors have been encountered during the verify operation

31.4.6.16 Erase EEPROM Sector Command

The Erase EEPROM Sector operation will erase all addresses in a sector of the EEPROM block.

Table A-24. ADC Conversion Performance 5V range (Junction Temperature From +150°C To +160°C)

S12GN16, S12GN32								
Supply voltage 4.5V < V_{DDA} < 5.5 V, 150°C < T_J < 160°C, V_{REF} = V_{RH} - V_{RL} = V_{DDA}, f_{ADCCLK} = 8.0MHz The values are tested to be valid with no port AD output drivers switching simultaneous with conversions.								
Num	**C**	**Rating**[1]		**Symbol**	**Min**	**Typ**	**Max**	**Unit**
1	M	Resolution	10-Bit	LSB		5		mV
2	M	Differential Nonlinearity	10-Bit	DNL		±0.5		counts
3	M	Integral Nonlinearity	10-Bit	INL		±1		counts
4	M	Absolute Error[2]	10-Bit[3] 10-Bit[4]	AE		±2 ±2		counts
5	C	Resolution	8-Bit	LSB		20		mV
6	C	Differential Nonlinearity	8-Bit	DNL		±0.3		counts
7	C	Integral Nonlinearity	8-Bit	INL		±0.5		counts
8	C	Absolute Error[2]	8-Bit	AE		±1		counts

1 The 8-bit mode operation is structurally tested in production test. Absolute values are tested in 10-bit mode.

2 These values include the quantization error which is inherently 1/2 count for any A/D converter.

3 LQFP 48 and bigger

4 LQFP 32 and smaller

Table A-25. ADC Conversion Performance 3.3V range (Junction Temperature From –40°C To +150°C)

S12GNA16, S12GNA32, S12GAS48, S12GA64, S12GA96, S12GA128, S12GA192 and S12GA240								
Supply voltage 3.13V < V_{DDA} < 4.5 V, -40°C < T_J < 150°C, V_{REF} = V_{RH} - V_{RL} = V_{DDA}, f_{ADCCLK} = 8.0MHz The values are tested to be valid with no port AD output drivers switching simultaneous with conversions.								
Num	**C**	**Rating**[1]		**Symbol**	**Min**	**Typ**	**Max**	**Unit**
1	P	Resolution	12-Bit	LSB		0.80		mV
2	P	Differential Nonlinearity	12-Bit	DNL	-6	±3	6	counts
3	P	Integral Nonlinearity	12-Bit	INL	-7	±3	7	counts
4	P	Absolute Error[2]	12-Bit	AE	-8	±4	8	counts
5	C	Resolution	10-Bit	LSB		3.22		mV
6	C	Differential Nonlinearity	10-Bit	DNL	-1.5	±1	1.5	counts
7	C	Integral Nonlinearity	10-Bit	INL	-2	±1	2	counts
8	C	Absolute Error[2]	10-Bit	AE	-3	±2	3	counts
9	C	Resolution	8-Bit	LSB		12.89		mV
10	C	Differential Nonlinearity	8-Bit	DNL	-0.5	±0.3	0.5	counts
11	C	Integral Nonlinearity	8-Bit	INL	-1	±0.5	1	counts
12	C	Absolute Error[2]	8-Bit	AE	-1.5	±1	1.5	counts

1 The 8-bit and 10-bit mode operation is structurally tested in production test. Absolute values are tested in 12-bit mode.

NOTES:

1. ALL DIMENSIONS ARE IN MILLIMETERS.

2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M–1994.

3. DATUMS B, C AND D TO BE DETERMINED AT DATUM PLANE H.

4. THE TOP PACKAGE BODY SIZE MAY BE SMALLER THAN THE BOTTOM PACKAGE SIZE BY A MAXIMUM OF 0.1 mm.

5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD PROTRUSIONS. THE MAXIMUM ALLOWABLE PROTRUSION IS 0.25 mm PER SIDE. D1 AND E1 ARE MAXIMUM BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH.

6. DIMENSION b DOES NOT INCLUDE DAM BAR PROTRUSION. PROTRUSIONS SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.35. MINIMUM SPACE BETWEEN PROTRUSION AND AN ADJACENT LEAD SHALL BE 0.07 MM.

7. DIMENSIONS D AND E ARE DETERMINED AT THE SEATING PLANE, DATUM A.

MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE

TITLE:	DOCUMENT NO: 98ASS23308W	REV: H
100 LEAD LQFP 14 X 14, 0.5 PITCH, 1.4 THICK	CASE NUMBER: 983–02	25 MAY 2005
	STANDARD: NON–JEDEC	